In the Claims:

Please amend the claims as follows:

- 1. (original) A diamond-coated silicon comprising a silicon substrate having a thickness of 500 μ m or less coated at least partially with electrically conductive diamond, wherein the silicon substrate is manufactured by the plate-like crystal growth process.
- 2. (original) The diamond-coated silicon according to claim 1, wherein the plate-like crystal growth process is at least one selected from the EFG process, the string ribbon process and the dendritic web process.
- 3. (currently amended) The diamond-coated silicon according to claim 1 or 2, wherein the silicon substrate is single crystalline, polycrystalline or amorphous.
- 4. (currently amended) The diamond-coated silicon according to <u>claim 1</u> any one of <u>claims 1 to 3</u>, wherein the silicon substrate is coated with electrically conductive diamond by the chemical vapor deposition process.
- 5. (currently amended) A manufacturing method of a diamond-coated silicon comprising coating a silicon substrate having a thickness of 500 μm or less at least partially with

electrically conductive diamond by \underline{a} the chemical vapor deposition process.

- (currently amended) A manufacturing method of a diamond-coated silicon comprising the steps of;
- (a) a step for manufacturing a silicon substrate having a thickness of 500 μm or less by a the plate-like crystal growth process; and
- (e) a step for coating the manufactured silicon substrate at least partially with electrically conductive diamond by chemical vapor deposition process.
- 7. (currently amended) The manufacturing method of a diamond-coated silicon according to claim 6, wherein the plate-like crystal growth process is at least one selected from the group consisting of: an EFG process, the a string ribbon process and the a dendritic web process.
- 8. (currently amended) The manufacturing method of a diamond-coated silicon according to claim 6 or 7, wherein the step (a) and the step (e) are successively carried out.
- 9. (currently amended) The manufacturing method of a diamond-coated silicon according to $\underline{\text{claim 6}}$ any one of claims—6 to 8, further comprising, between the step (a) and the step (e),

- (d) a step for controlling a pressure at least once.
- 10. (currently amended) The manufacturing method of a diamond-coated silicon according to claim 6 any one of claims 6 to 9, further comprising, after the step (e),
 - (f) a step for controlling a pressure at least once.
- 11. (currently amended) The manufacturing method of a diamond-coated silicon according to claim 6 any one of claims 6, 7, 9 and 10, further comprising, between the step (a) and the step (b), or between the step (d) and the step (e) when present,
 - (b) a step for winding the silicon substrate; and
- $\mbox{(c)} \quad \mbox{a step for supplying the wound silicon substrate}$ to a chemical vapor deposition device.
- 12. (currently amended) The manufacturing method of a diamond-coated silicon according to claim 6 any one of claims 6 to 11, further comprising, after the step (e), or after the step (f) when present,
 - (g) a step for winding a diamond-coated silicon.
- 13. (new) The diamond-coated silicon according to claim 2, wherein the silicon substrate is single crystalline, polycrystalline or amorphous.

- 14. (new) The diamond-coated silicon according to claim 2, wherein the silicon substrate is coated with electrically conductive diamond by the chemical vapor deposition process.
- 15. (new) The diamond-coated silicon according to claim 3, wherein the silicon substrate is coated with electrically conductive diamond by the chemical vapor deposition process.
- 16. (new) The manufacturing method of a diamond-coated silicon according to claim 7, wherein the step (a) and the step (e) are successively carried out.
- 17. (new) The manufacturing method of a diamond-coated silicon according to claim 7, further comprising, between the step (a) and the step (e):
 - (d) a step for controlling a pressure at least once.
- 18. (new) The manufacturing method of a diamond-coated silicon according to claim 8, further comprising, between the step (a) and the step (e):
 - (d) a step for controlling a pressure at least once.
- 19. (new) The manufacturing method of a diamond-coated silicon according to claim 7, further comprising, after the step (e):

- (f) a step for controlling a pressure at least once.
- 20. (new) The manufacturing method of a diamond-coated silicon according to claim 8, further comprising, after the step (e):
 - (f) a step for controlling a pressure at least once.
- 21. (new) The manufacturing method of a diamond-coated silicon according to claim 9, further comprising, after the step (e):
 - (f) a step for controlling a pressure at least once.
- 22. (new) The manufacturing method of a diamond-coated silicon according to claim 7, further comprising, between the step (a) and the step (e):
 - (b) a step for winding the silicon substrate; and
- (c) a step for supplying the wound silicon substrate to a chemical vapor deposition device.
- 23. (new) The manufacturing method of a diamond-coated silicon according to claim 8, further comprising, between the step (a) and the step (e):
 - (b) a step for winding the silicon substrate; and
- (c) a step for supplying the wound silicon substrate to a chemical vapor deposition device.

- 24. (new) The manufacturing method of a diamond-coated silicon according to claim 9, further comprising, between the step (d) and the step (e):
 - (b) a step for winding the silicon substrate; and
- (c) a step for supplying the wound silicon substrate to a chemical vapor deposition device.
- 25. (new) The manufacturing method of a diamond-coated silicon according to claim 10, further comprising, between the step (a) and the step (e):
 - (b) a step for winding the silicon substrate; and
- (c) a step for supplying the wound silicon substrate to a chemical vapor deposition device.
- 26. (new) The manufacturing method of a diamond-coated silicon according to claim 7, further comprising, after the step (e):
 - (g) a step for winding a diamond-coated silicon.
- 27. (new) The manufacturing method of a diamond-coated silicon according to claim 8, further comprising, after the step (e):
 - (g) a step for winding a diamond-coated silicon.

- 28. (new) The manufacturing method of a diamond-coated silicon according to claim 9, further comprising, after the step (e):
 - (g) a step for winding a diamond-coated silicon.
- 29. (new) The manufacturing method of a diamond-coated silicon according to claim 10, further comprising, after the step (f):
 - (g) a step for winding a diamond-coated silicon.
- 30. (new) The manufacturing method of a diamond-coated silicon according to claim 11, further comprising, after the step (e):
 - (g) a step for winding a diamond-coated silicon.